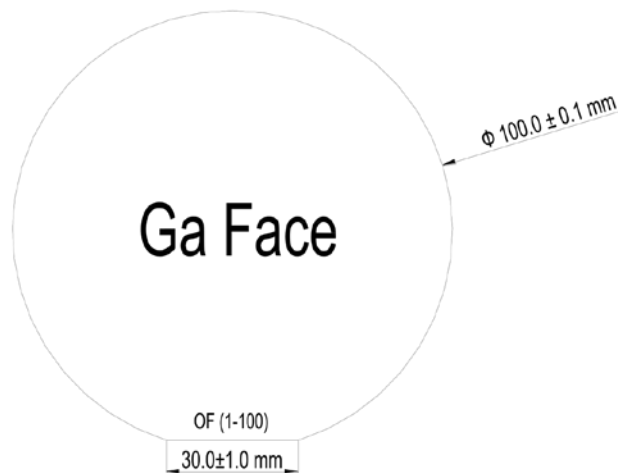


4 inch GaN on Sapphire Templates



性能参数 Specifications:

产品型号 Item	GaN-T-C-U-C100	GaN-T-C-N-C100
尺寸 Dimensions	Φ 100 mm ± 0.1 mm	
厚度 Thickness	4.5±0.5 μm, 20 μm	
晶体取向 Orientation	C-plane(0001) ± 0.5°	
导电类型 Conduction Type	N-type (Undoped)	N-type (Si-doped)
电阻率 Resistivity(300K)	< 0.5 Ω·cm	< 0.05 Ω·cm
载流子浓度 Carrier Concentration	< 5x10 ¹⁷ cm ⁻³	> 1x10 ¹⁸ cm ⁻³
迁移率 Mobility	~ 300 cm ² /V·s	~ 200 cm ² /V·s
位错密度 Dislocation Density	Less than 5x10 ⁸ cm ⁻² (calculated by FWHMs of XRD)	
衬底结构 Substrate structure	GaN on Sapphire(Standard: SSP Option: DSP)	
有效面积 Useable Surface Area	> 90%	
包装 Package	Packaged in a class 100 clean room environment, in cassettes of 25pcs or single wafer containers, under a nitrogen atmosphere.	



2 inch GaN on Sapphire Templates



性能参数 Specifications:

产品型号 Item	GaN-T-C-U-C50	GaN-T-C-N-C50	GaN-T-C-P-C50
尺寸 Dimensions	Φ 50.8mm ± 0.1mm		
厚度 Thickness	4.5±0.5 μm, 20±2 μm		4.5±0.5μm
晶体取向 Orientation	C-plane(0001) ± 0.5°		
导电类型 Conduction Type	N-type (Undoped)	N-type (Si-doped)	P-type (Mg-doped)
电阻率 Resistivity(300K)	< 0.5 Ω·cm	< 0.05 Ω·cm	~ 10 Ω·cm
载流子浓度 Carrier Concentration	< 5x10 ¹⁷ cm ⁻³	> 1x10 ¹⁸ cm ⁻³	> 6x10 ¹⁶ cm ⁻³
迁移率 Mobility	~ 300 cm ² /V·s	~ 200 cm ² /V·s	~ 10 cm ² /V·s
位错密度 Dislocation Density	Less than 5x10 ⁸ cm ⁻² (calculated by FWHMs of XRD)		
衬底结构 Substrate structure	GaN on Sapphire(Standard: SSP Option: DSP)		
有效面积 Useable Surface Area	> 90%		
包装 Package	Packaged in a class 100 clean room environment, in cassettes of 25pcs or single wafer containers, under a nitrogen atmosphere.		

